CLAIMS

1. A method of processing a wiring substrate that includes a configuration in which conductors locally disposed on a substrate are coated with resin having inorganic members that form a filler and are dispersed in an organic member, the method comprising:

removing the organic member from a surface layer side of the resin by use of an ashing method;

removing, by use of a wet cleaning method, the inorganic members remaining the surface layer side of the resin from which the organic member is removed;

forming a seed layer which serves foundation used to form conductors in a layered structure so that at least part thereof overlaps conductors having a surface layer portion that is exposed due to removal of the inorganic members; and

evaluating whether or not surfaces of the exposed conductors and a surface of resin surrounding the conductors are on a same plane by measuring a surface profile of the seed layer.

2. The method of processing a wiring substrate according to claim 1, wherein

removal of the organic member from the surface layer side of the resin is repeatedly carried out via the resin located at a position at which the conductors are covered therewith until surface layer portions of the conductors is observed.

3. The method of processing a wiring substrate according to claim 1 or claim 2, wherein

an ashing method used in removal of the organic member from the surface layer side of the resin is carried out while applying high-frequency power to the substrate, and

a bias RF output (W) of the high-frequency power is 0 to 1500.

4. The method of processing a wiring substrate according to any one of claims 1 to 3, wherein

an ashing method used in removal of the organic member from the surface layer side of the resin is carried out while applying high-frequency power to the substrate, and

a bias RF output density (W/cm^2) of the high-frequency power is 0.2 to 0.8.

5. The method of processing a wiring substrate according to any one of claims 1 to 4, wherein

an ashing method used in removal of the organic member from the surface layer side of the resin uses, as a processing gas, a mixed gas containing a gas selected from the group consisting of oxygen (O_2), nitrogen (N_2), and carbon tetrafluoride (CF_4).